

# Flip-Chip and Wafer Level Packaging Technologies

**Oswin Ehrmann**

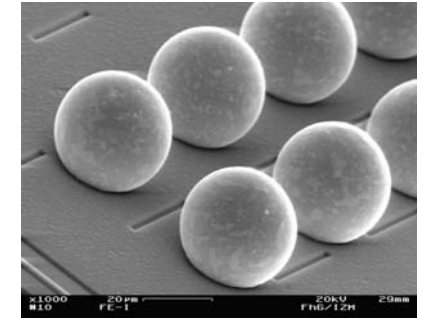
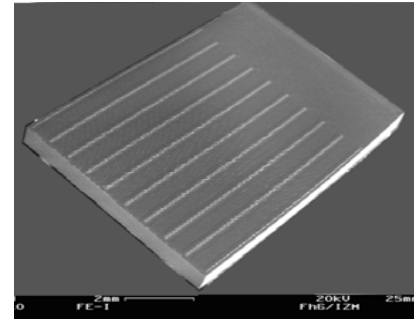
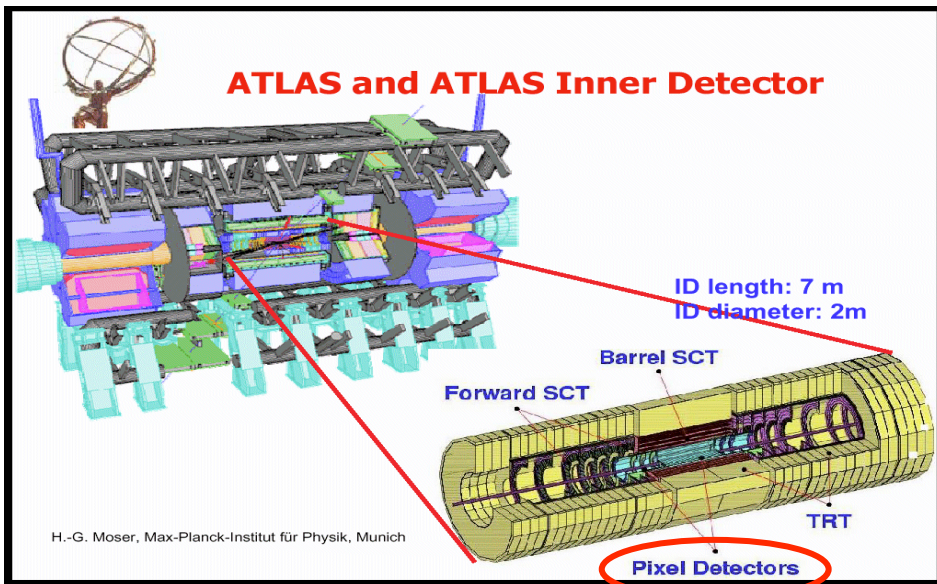
**Fraunhofer Institut for Reliability and Microintegration IZM  
D-13355 Berlin Germany  
Gustav-Meyer-Allee 25**

**ACES Workshop  
3./4. March 2009 CERN**

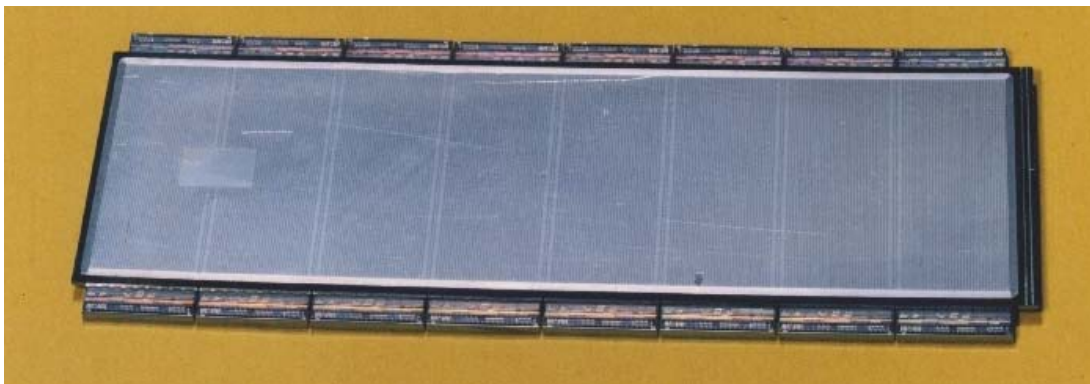
# Outline

- **Introduction**
- **Module Assembly Process**
  - Wafer Bumping
  - Flip Chip Bonding
  - New Requirements
- **3D Integration**
  - Thin Chip Integration
  - Through Silicon Vias (TSVs)

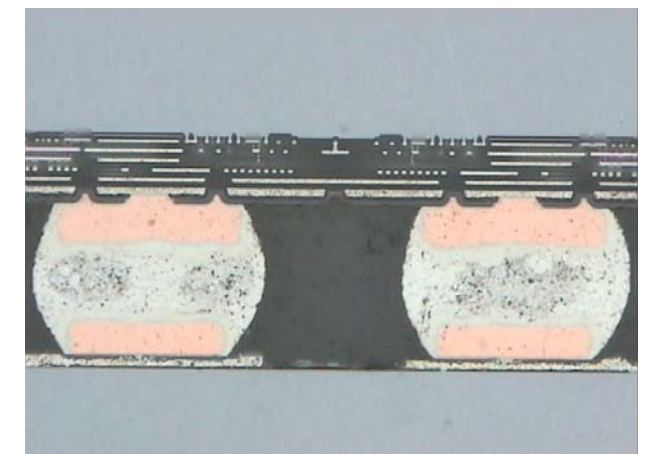
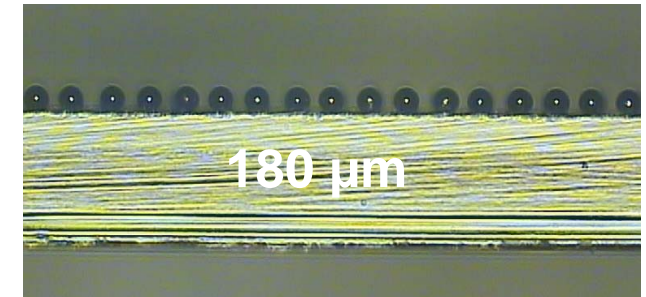
# Assembly of Modules: ATLAS Detector at LHC at CERN



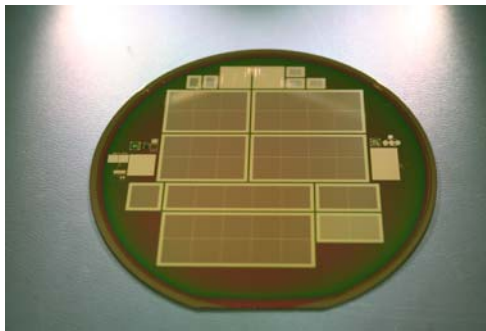
IBM 0.25  $\mu\text{m}$  rad tolerant design  
2800 Bumps/Chip 50 $\mu\text{m}$  Pitch



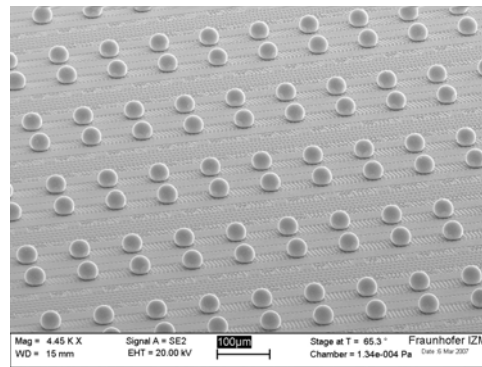
Thinning of  
bumped  
wafers:



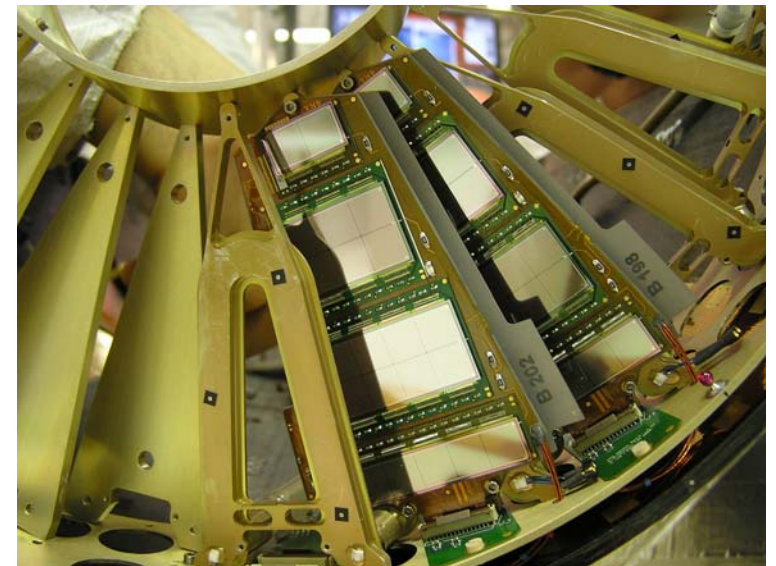
# Assembly of Modules: CMS Detector at LHC at CERN



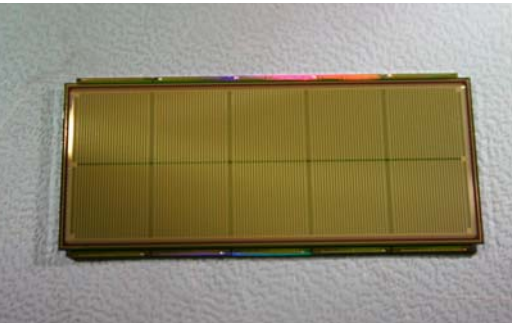
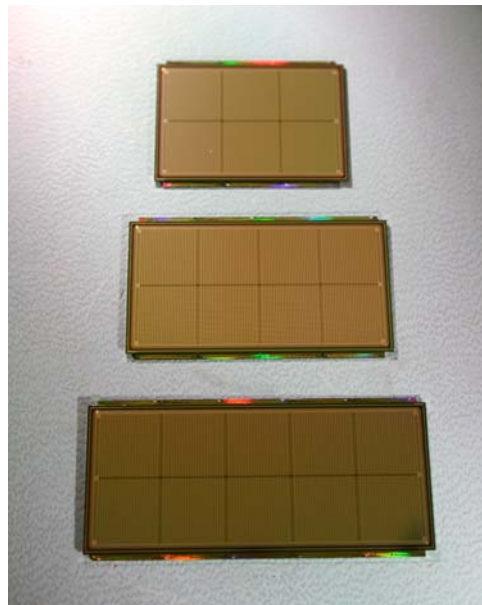
CMS pixel detector  
4inch sensor wafer



bumped CMS ROC



CMS silicon pixel detector  
endcap segments



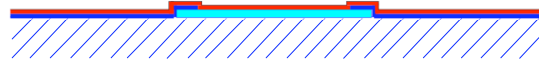
CMS pixel detector  
endcap modules after  
flip chip assembly

**More than 530 modules have been  
manufactured during production  
phase from October 2006 to  
February 2008**

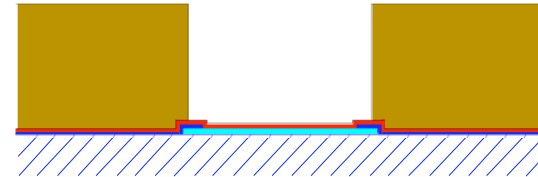




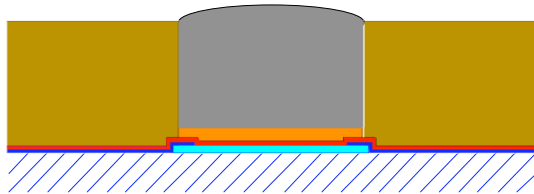
# Processflow: Bumping using Electroplating



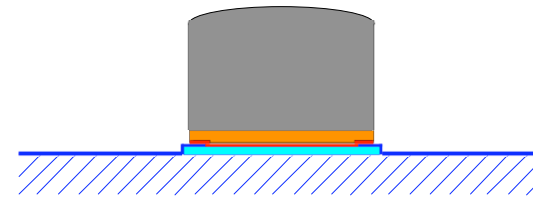
Sputter Etching and Sputtering of the Plating Base / UBM



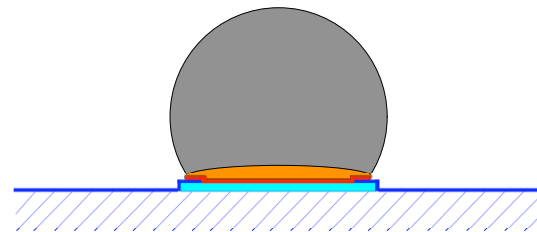
Spin Coating and Printing of Photoresist



Electroplating of Cu and Solder



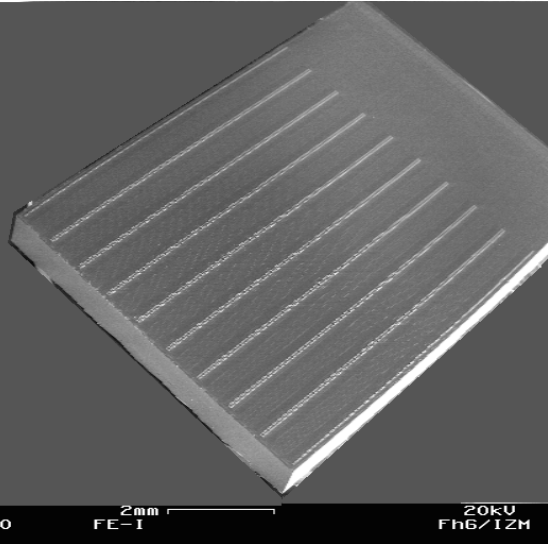
Resist Stripping and wetting of the Plating Base



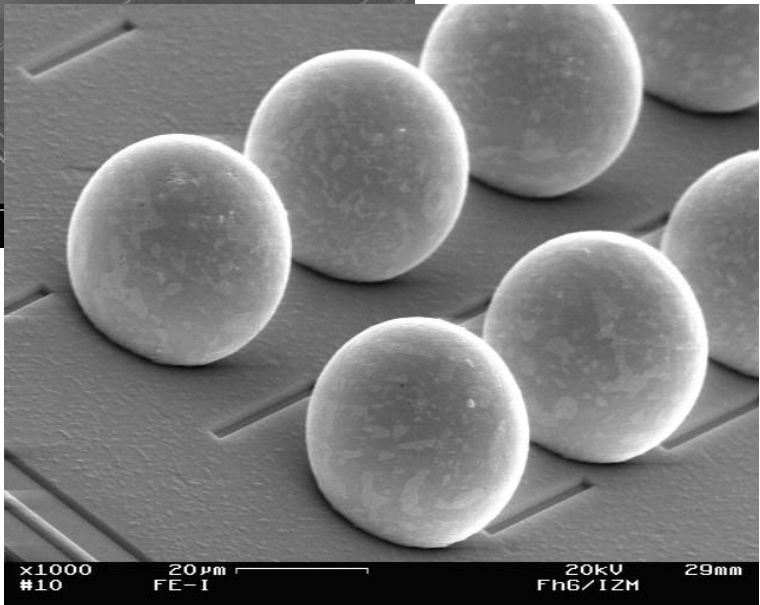
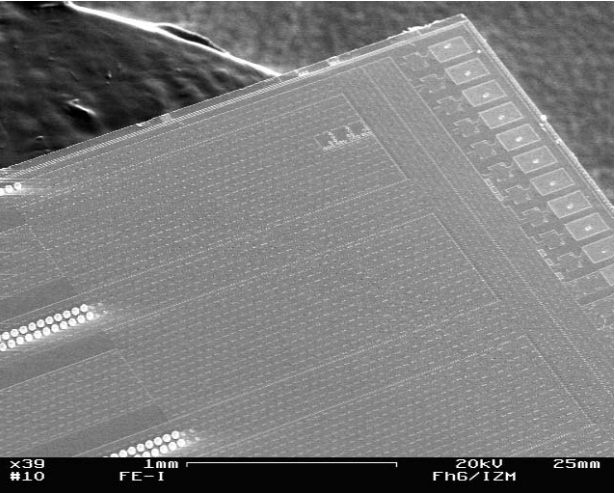
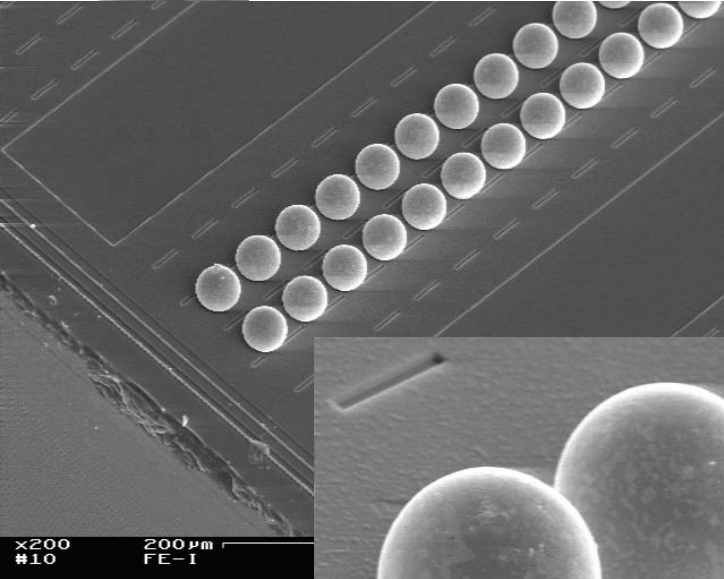
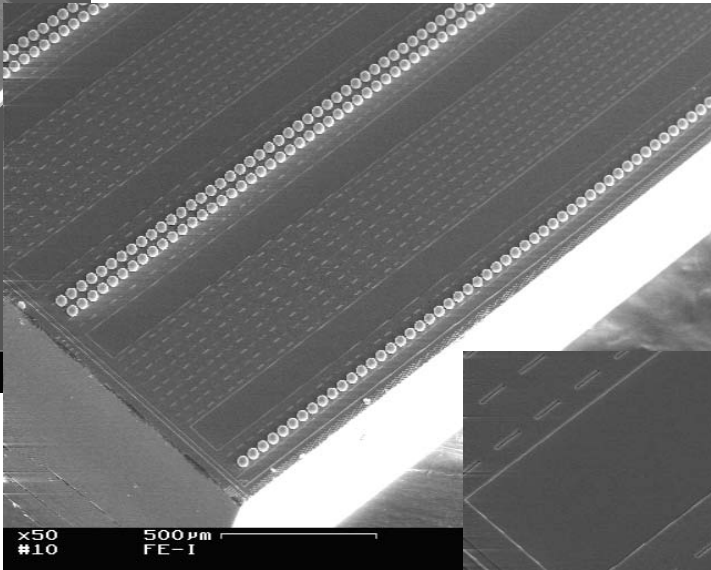
Reflow

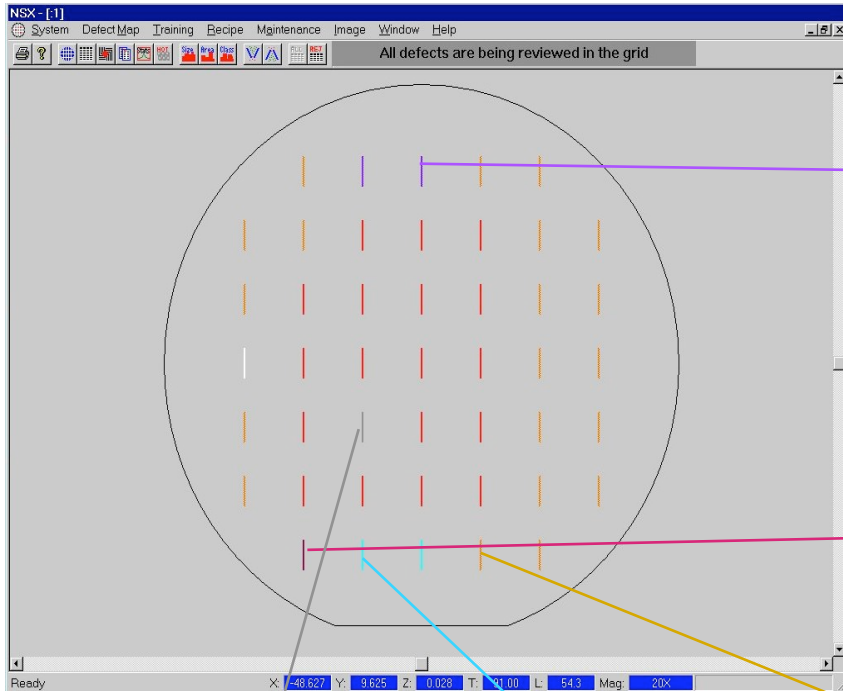
# Bumped FE-I Chip

## IBM 0.25 $\mu\text{m}$ rad tolerant design

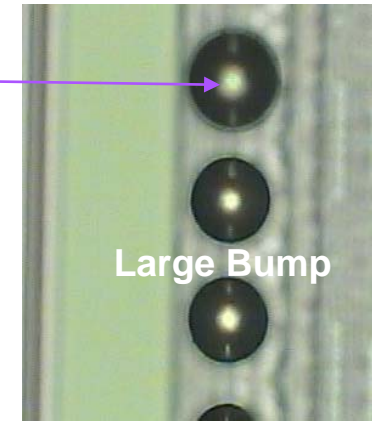


Chip with 9 column pairs

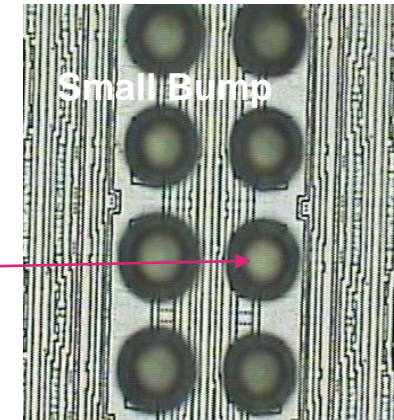




# Inspection

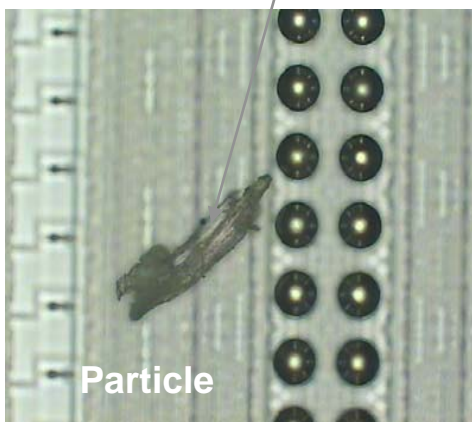


Large Bump

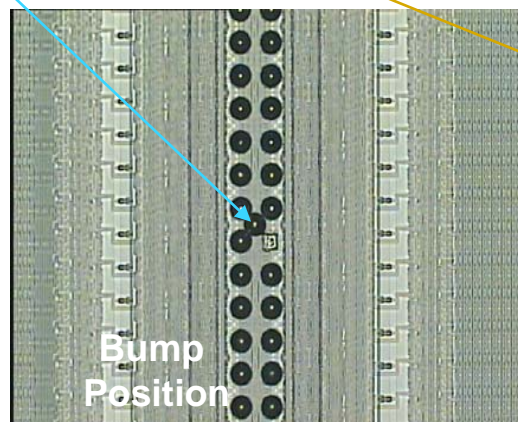


Small Bump

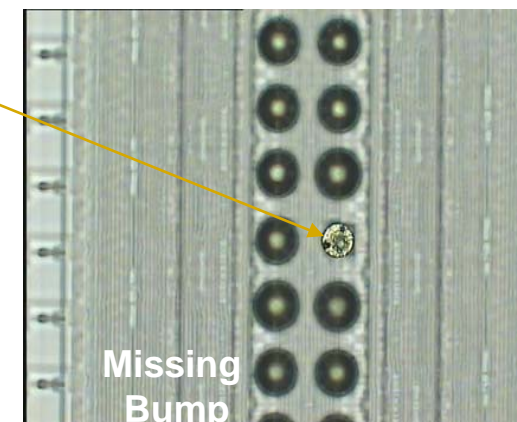
## Defect Classes



Particle



Bump Position



Missing Bump

# Assembly of ATLAS Pixel Detector Modules

- 16 ROC Flip-Chip Bonded to the Sensor
- 46 080 electroplated SnPb IO-Bumps, Ø 25 µm, pitch 50 µm
  
- Assembly of 1139 ATLAS Modules
- Assembled Chips: ~ 19000 chips
- Module Yield incl. rework: 97 %
- Chip Rework Rate: 0.7 %

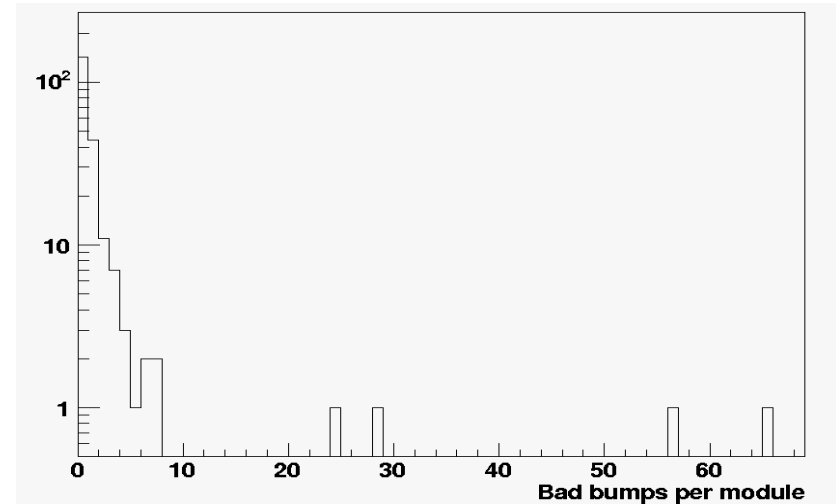
## Chip Yield after Bumping:

20.720 processed Readout Chips

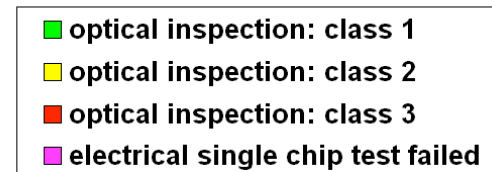
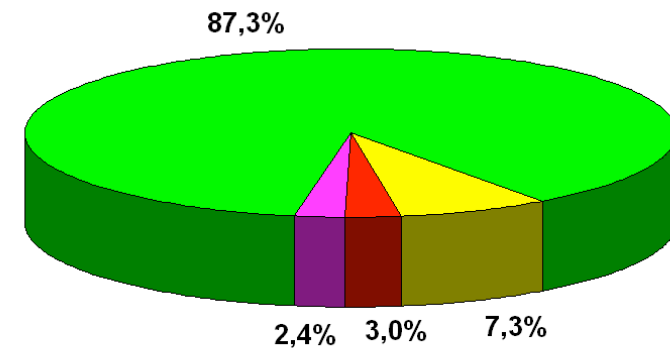
Class 1: perfect chips

Class 2: accepted defects  
( < 4 defective bumps, small particle, ...)

Class 3: rejected chips  
( > 4 defective bumps, scratches, residues, plating defects,...)



98% der Module mit <10 Bumpdefekten





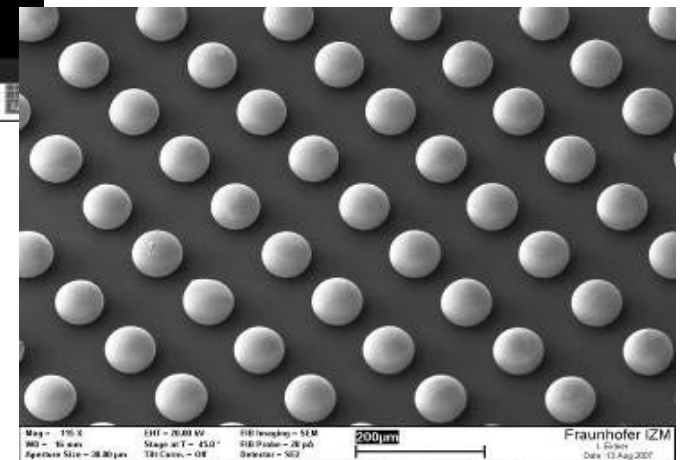
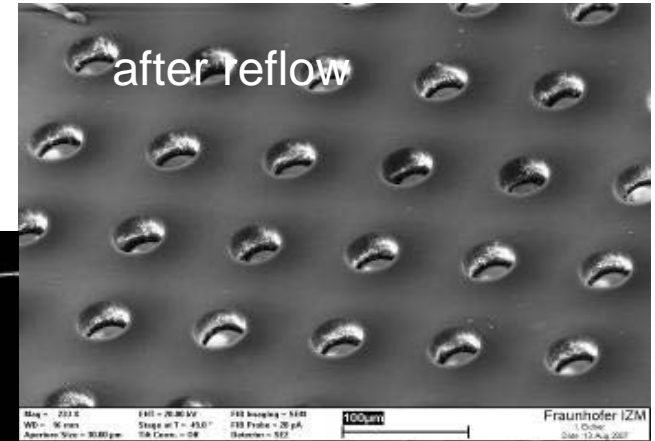
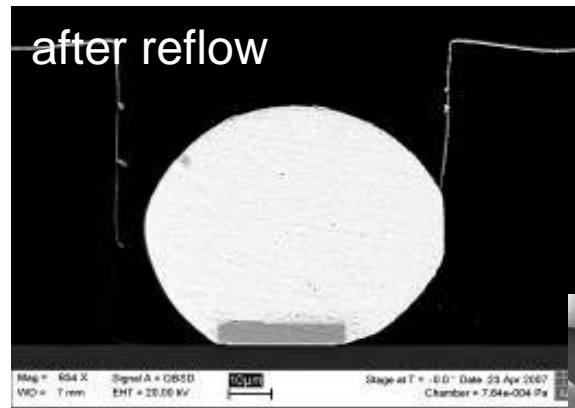
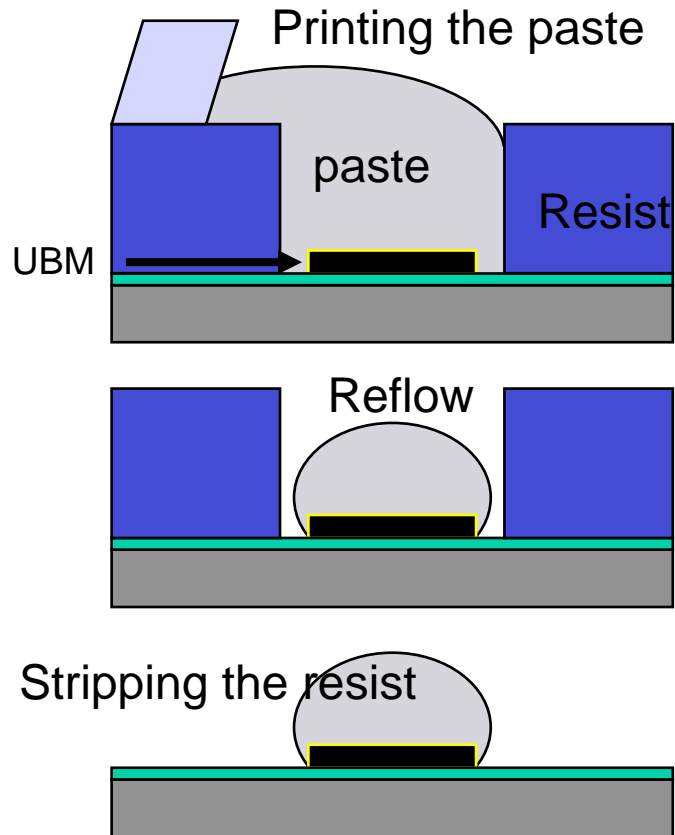
# Working Parts of the Module Assembly Process

- Bumping of the FE wafer
- Deposition of solderable pads on the sensor wafer
- Dicing
- Inspection
- Sorting for FC bonding
- Flip Chip Bonding
- Inspection

# Processes for Waferbumping

- Electroplating
- electroless deposition of Nickel pads (UBM)
- Stencil printing of solder paste →
- placement of preformed solder balls
- C4NP
- bonding by adhesives

# Waferbumping by Solderpaste Printing in Laminated Resist:



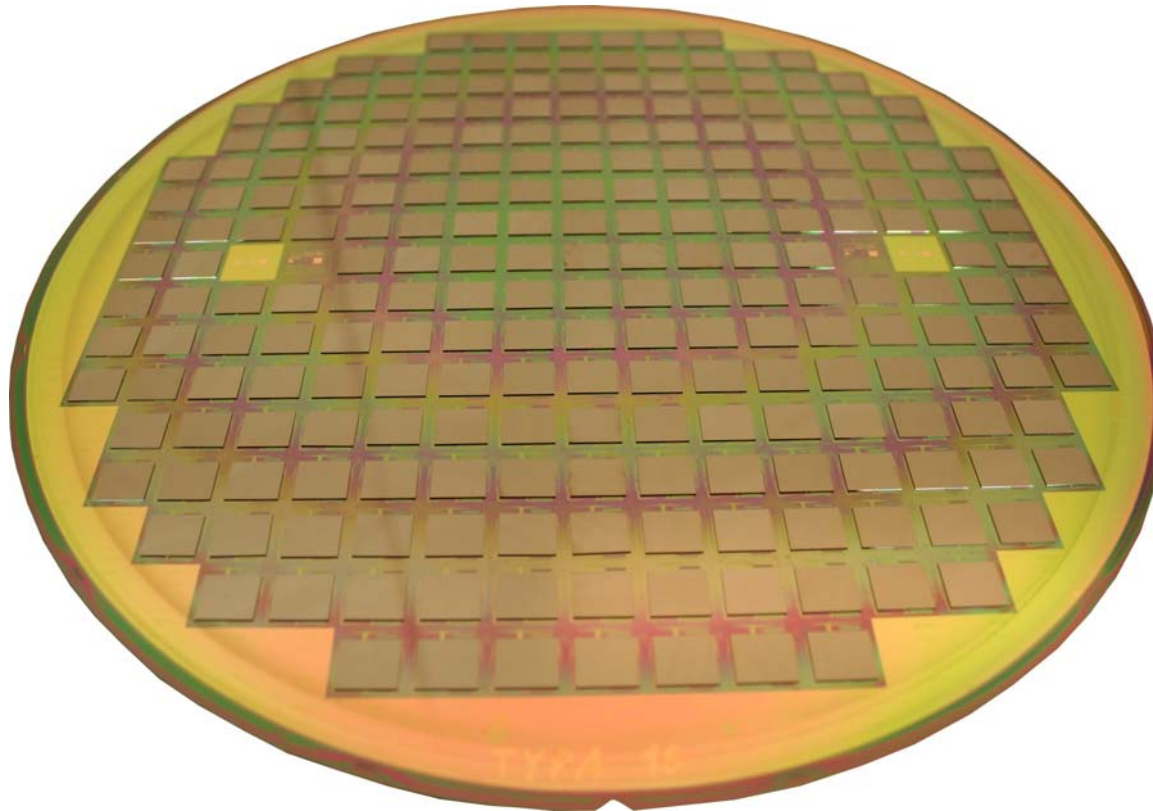
# Processes for Waferbumping

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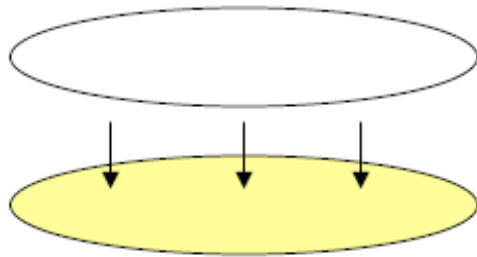


# Reduce Handling: Chip to Wafer FC-Mounting

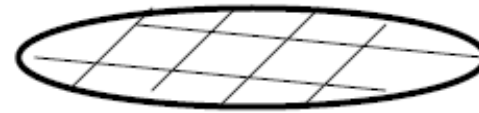
FC of thinned die on 8" Wafer



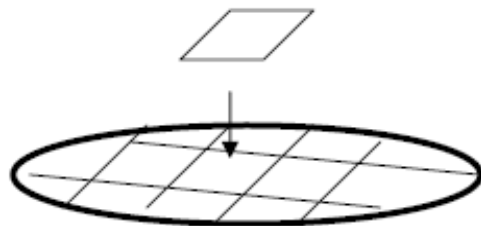
# Reduce Handling: Chip to Wafer FC-Mounting



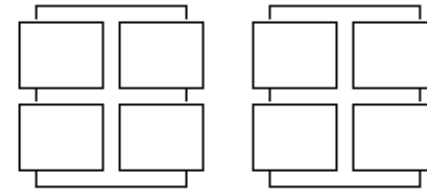
**Mounting sensor wafer to support wafer**



**Dicing of sensor wafer without cutting the support wafer**



**Flip chip bonding of bumped FE dies to the sensor**

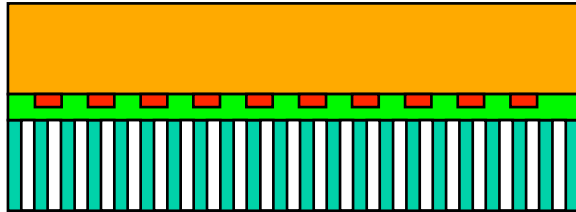


**Remove modules from support wafer**

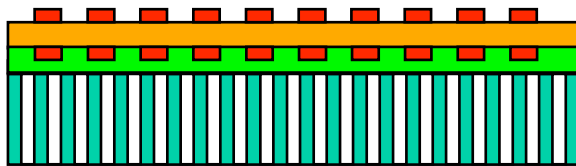
# Requirements:

- Large FE chips (1,68 x 2.0 cm<sup>2</sup>)
- Lager sensor wafers 150mm (still thin)
- Small pitch (50µm - high bonding accuracy)
- Reduce material budget (thinner FE-dies)
- 3D Integration
- Reduce cost
- Low volume

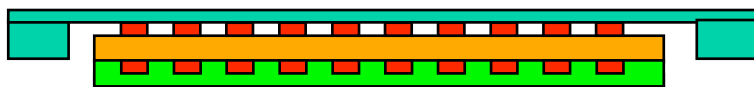
# Temporary Support Bonding for Thin Wafer Processing



Temporary Support Bonding



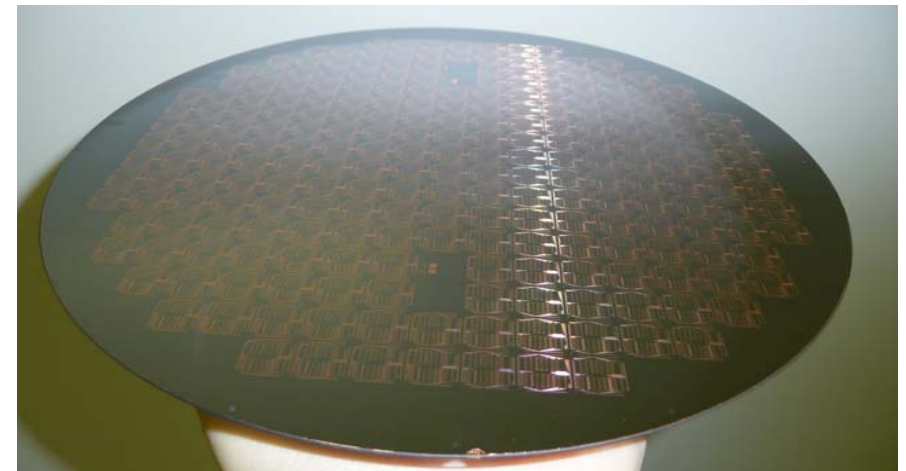
Thinning and backside processing



Debonding

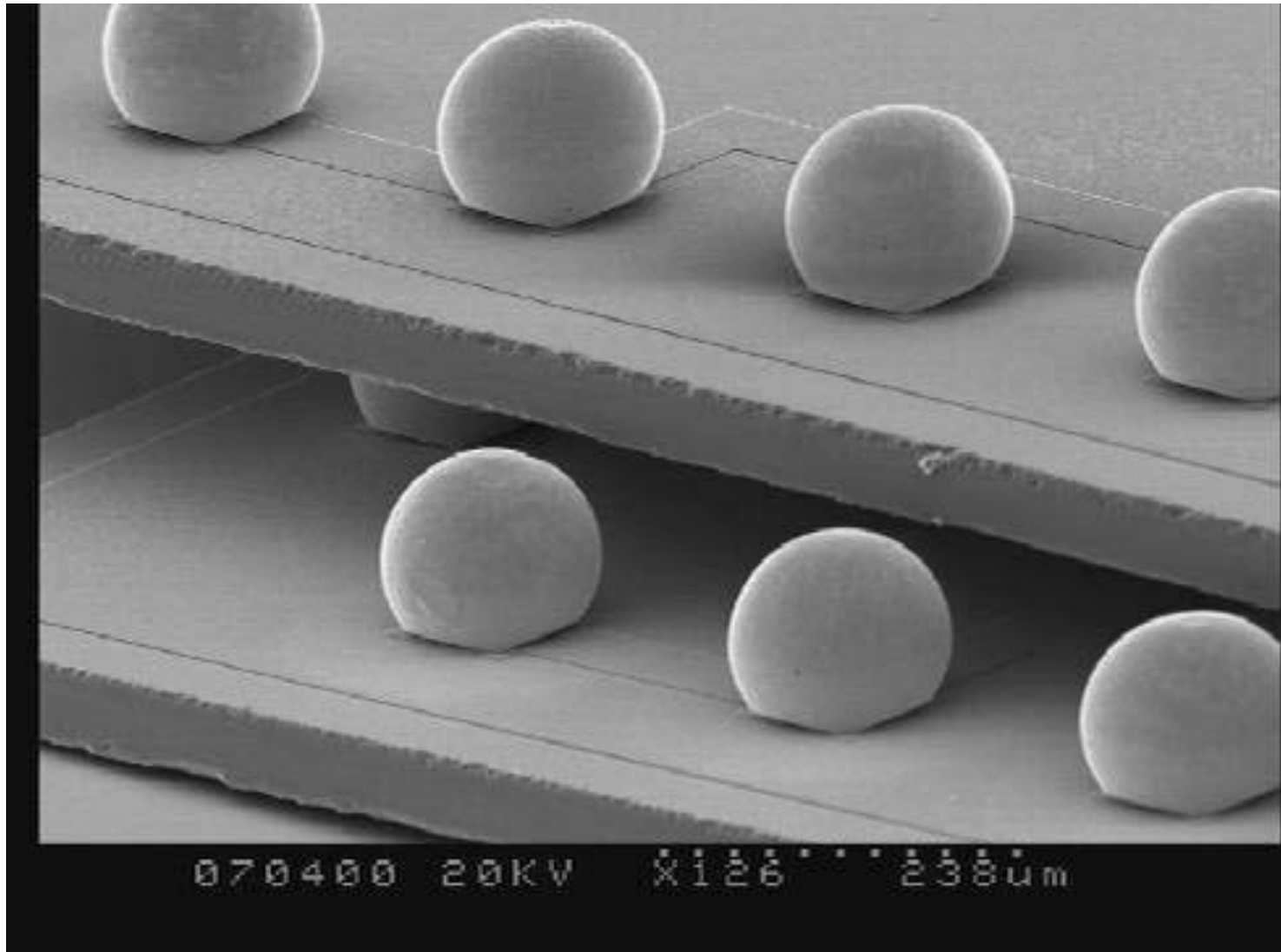


Support Wafer

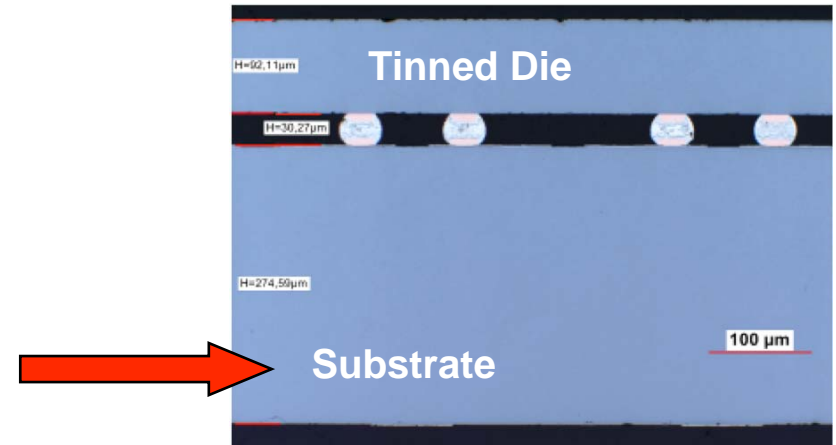
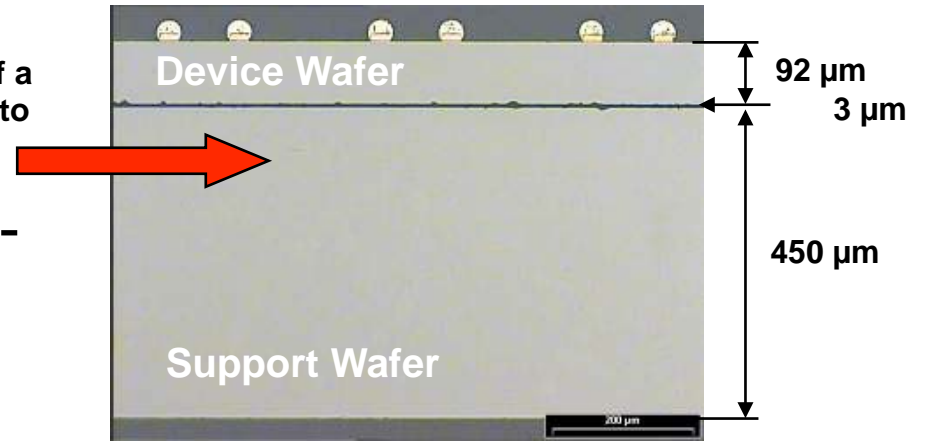
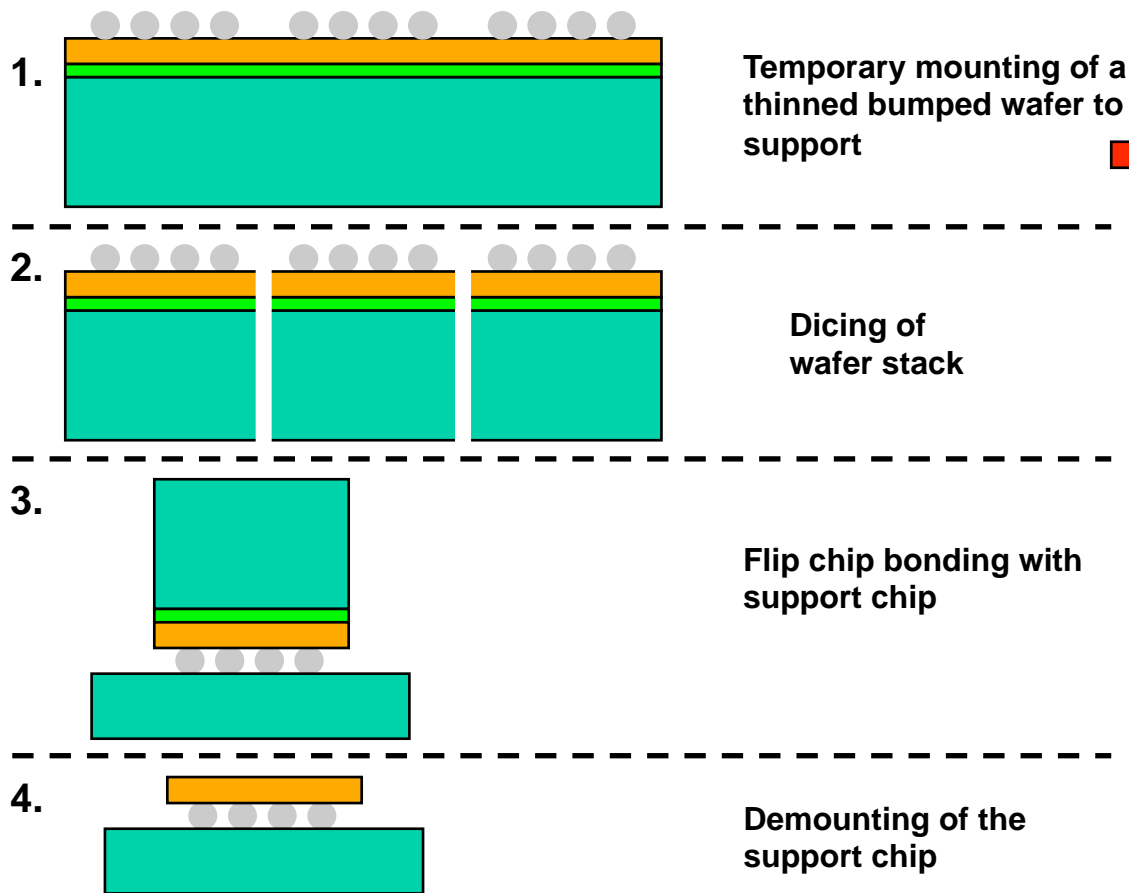


200mm wafer thinned down to 60μm and backside metallization



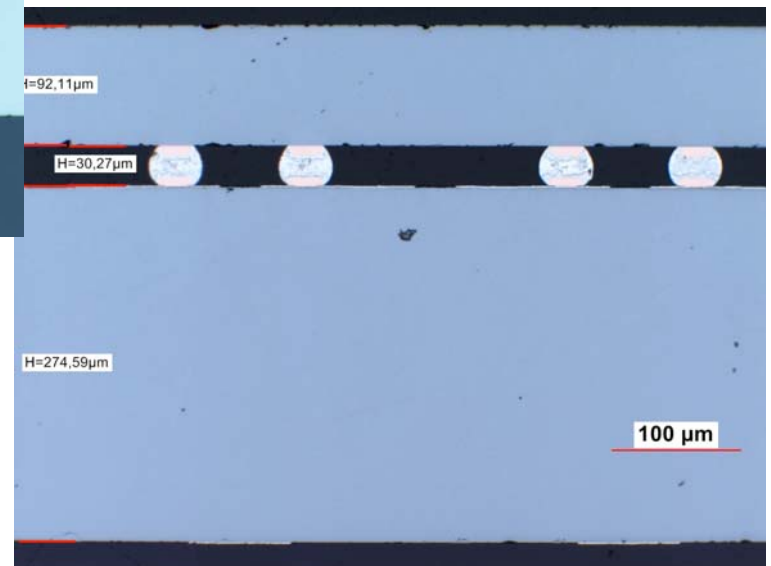
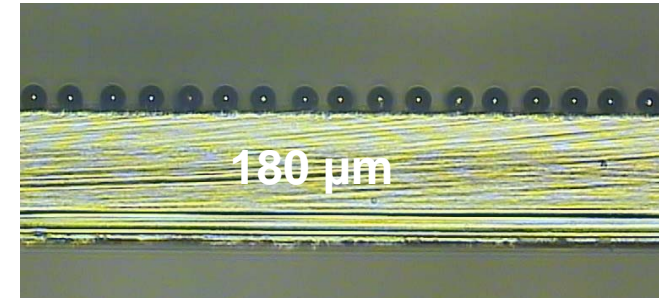


# Temporary Support Bonding for Assembly of Thin Chips

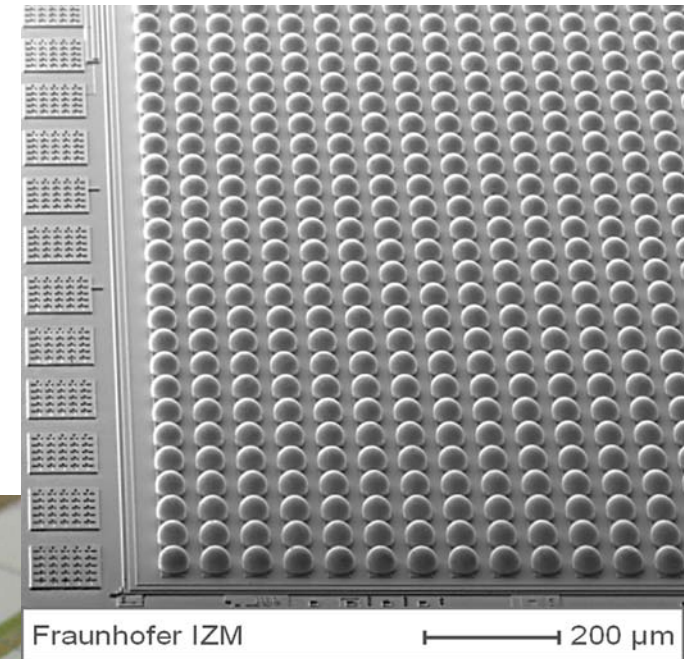
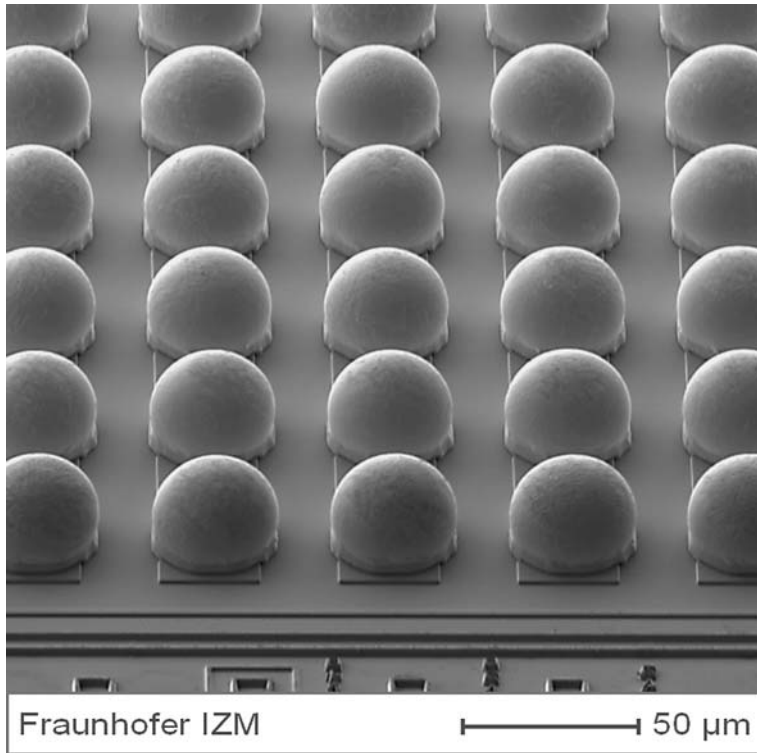


# Future Requirements: Thin Silicon

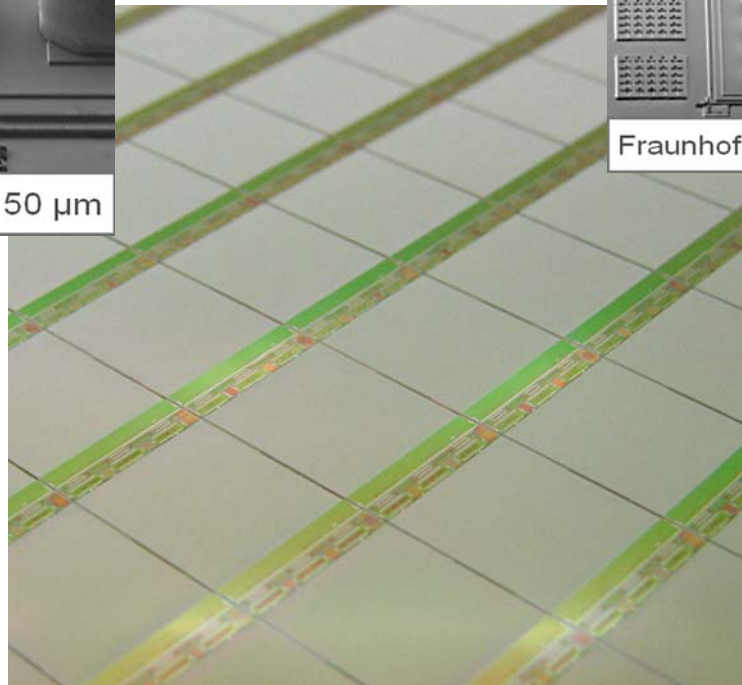
## Thinning of bumped wafers:



90μm FE Chips  
assembled

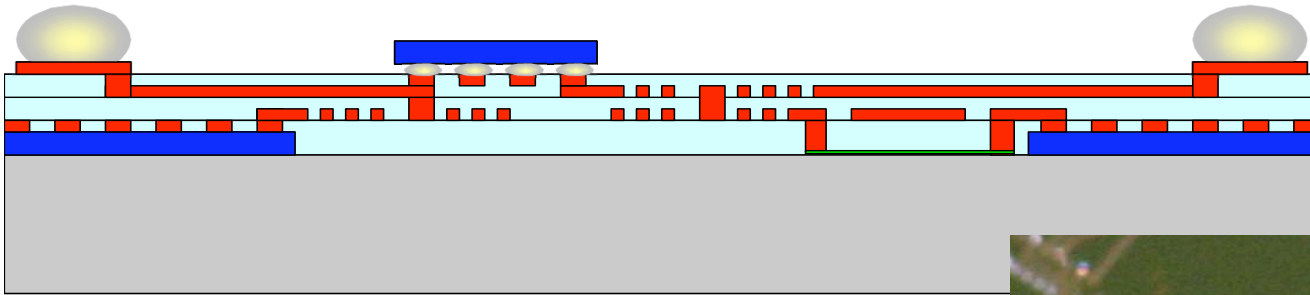


# Lead Free Bumping SnAg

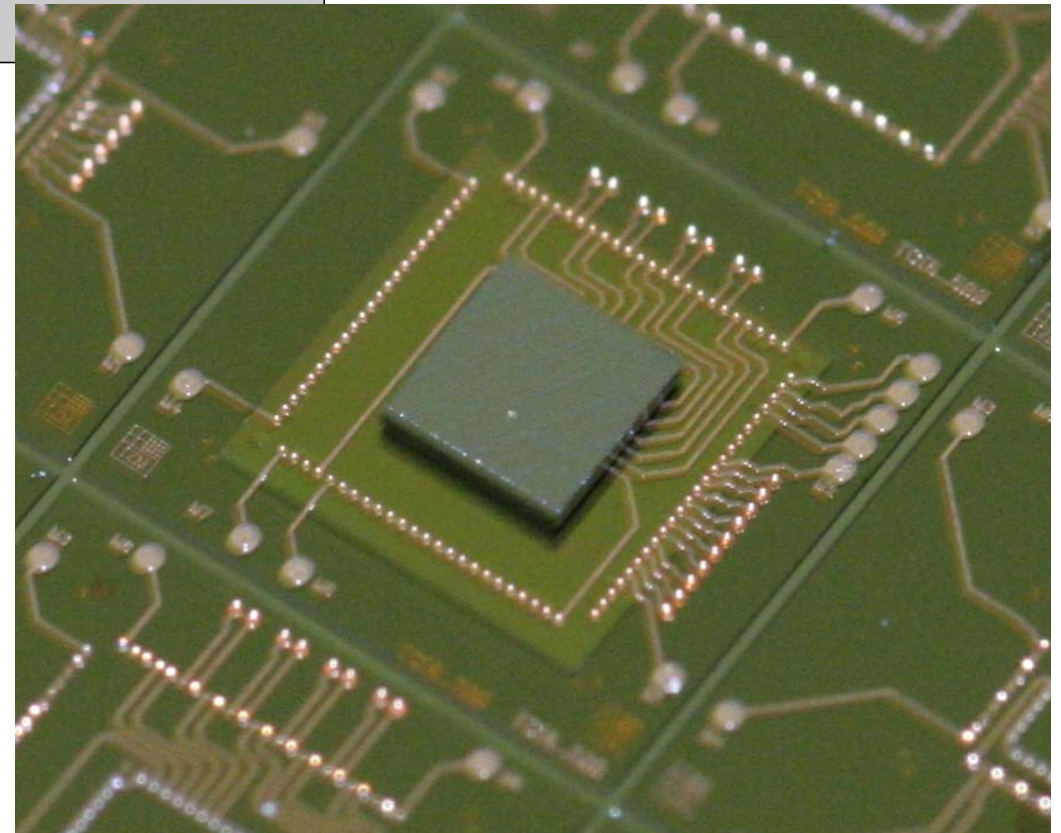




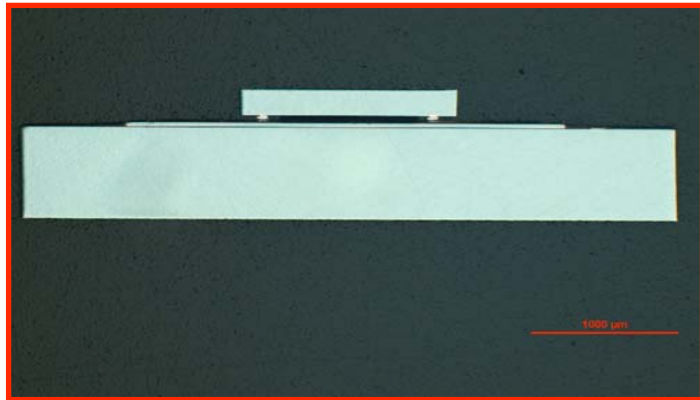
# 3D: Stacking by Thin Chip Integration



Combination of Flip Chip and embedding technology and integrated passive components



# Stacking by Thin Chip Integration

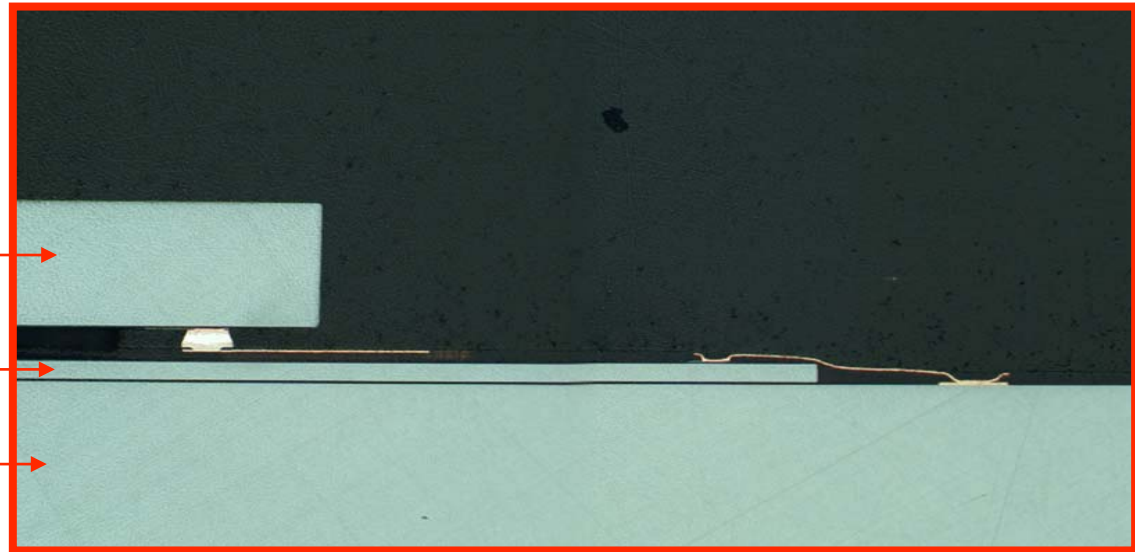


- Chip stacking of 3 Chips (Level 1 - 3)
- Thin Chip Assembly on Wafer Level – chip thickness 32µm
- BCB/Cu redistribution including thin chip embedding
- flip chip assembly of 190µm Chip on top of integrated thin chip

Level3: Daisy Chain Flip Chip

Level2: Thinned embedded Die

Level1: Substrate Chip



# Through Silicon Vias: Basic Questions

## Pre Front End Process – Post Front End Process

New Front End Process

Restrictions in Process Parameters

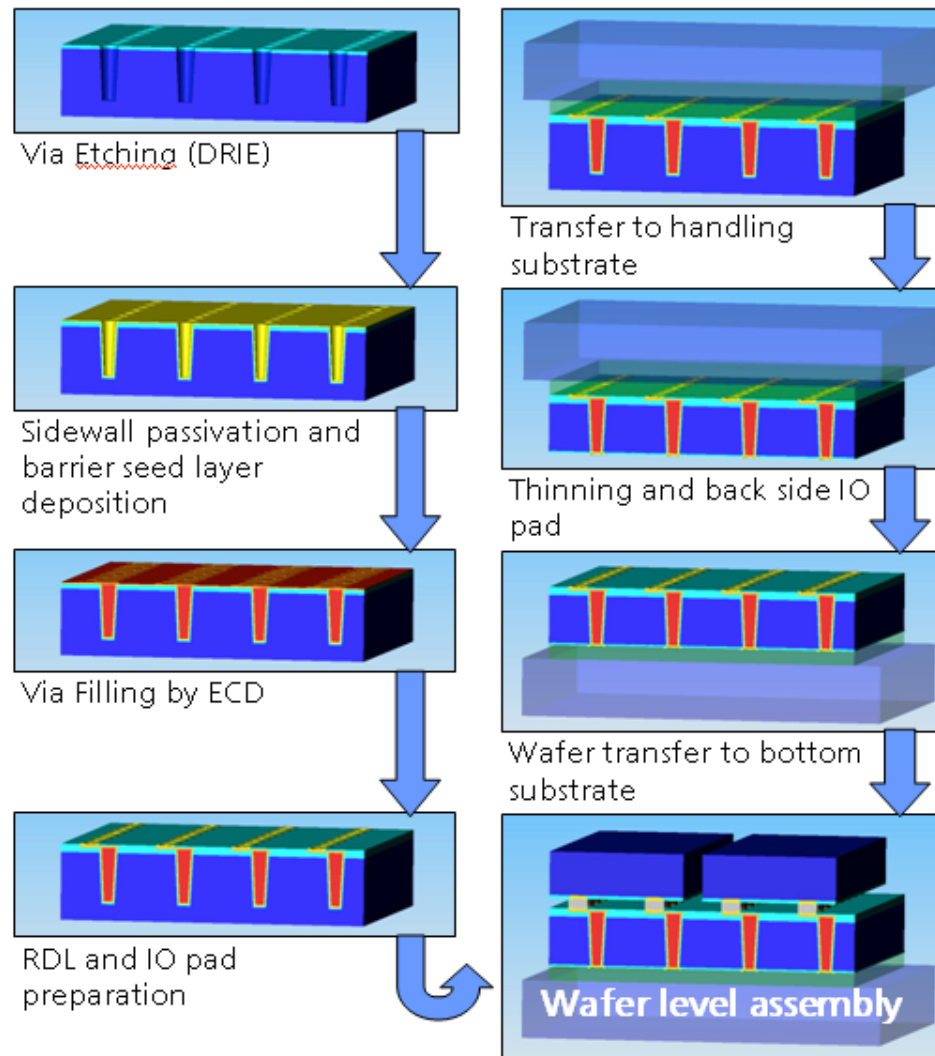
Design Restrictions

# Through Silicon Vias

## TSV – Formation and Metallization

- Deep Via High Aspect Ratio Etching ( $h > 20 \mu\text{m} - 200 \mu\text{m}$ )
- Side Wall Insulation
- Deposit Seed- and Barrier Layers
- Via Filling
- Wafer Thinning
- Front and Backside Metallization

# 3D Integration using Through Silicon Vias (TSVs) for High Density Interconnects in Stacked Devices

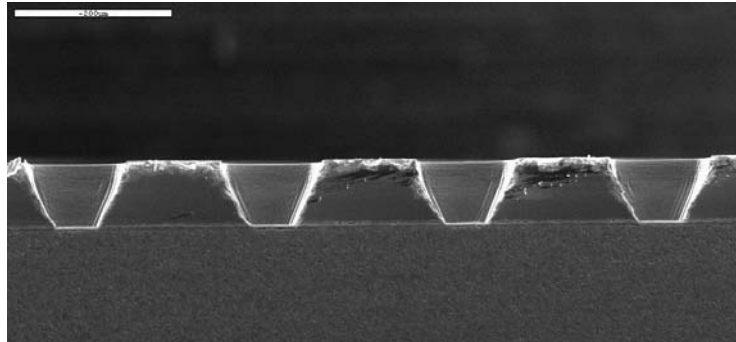


## Post Front-End TSV Process Flow

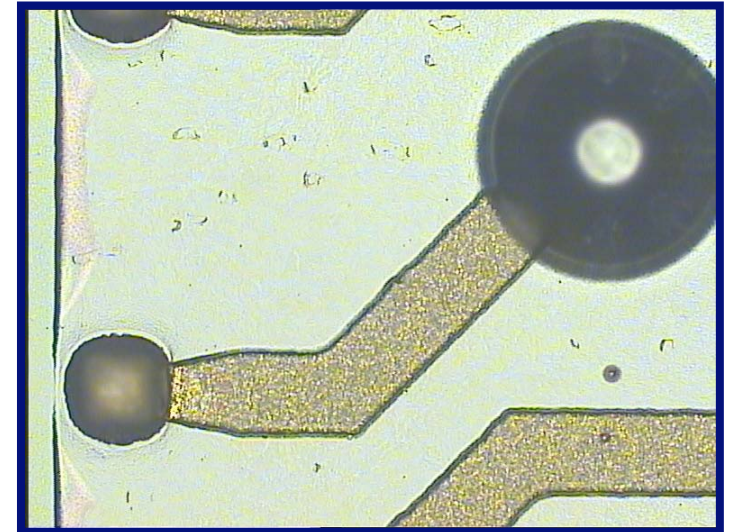
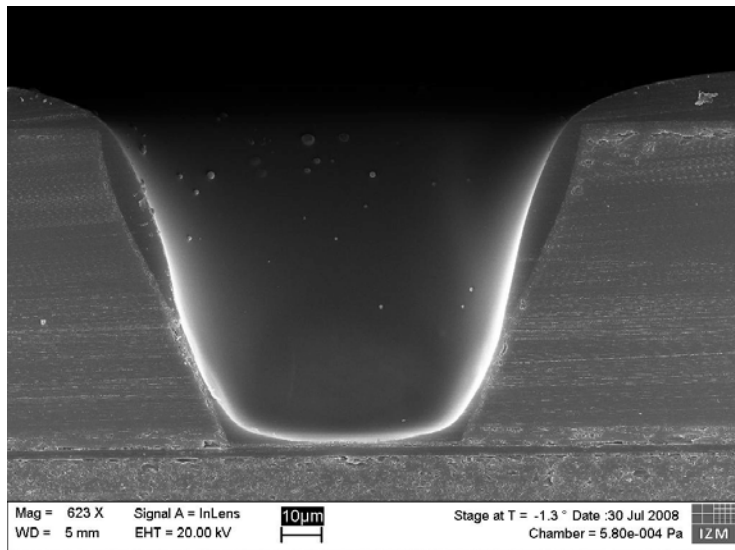


# Tapered Silicon Vias

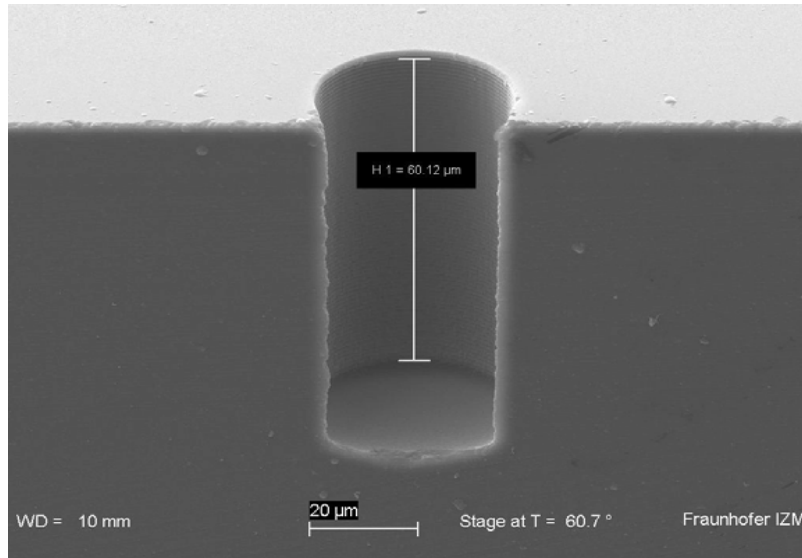
-- Low density backside contacts



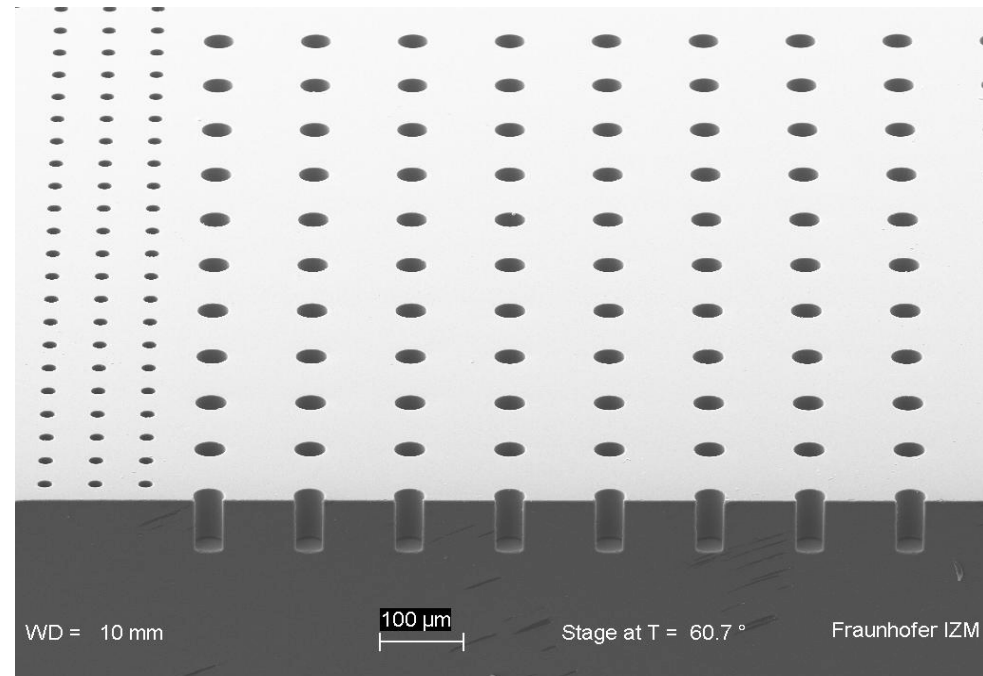
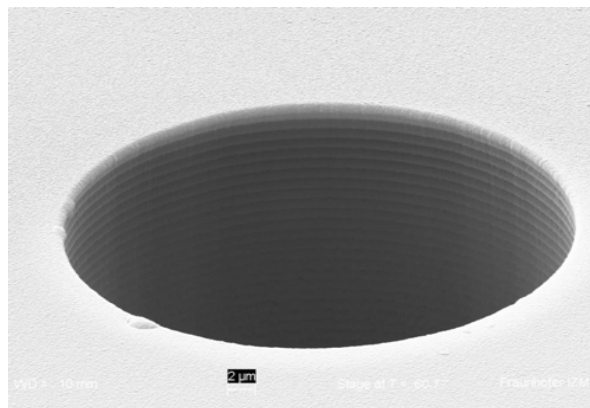
Etched  
Vias



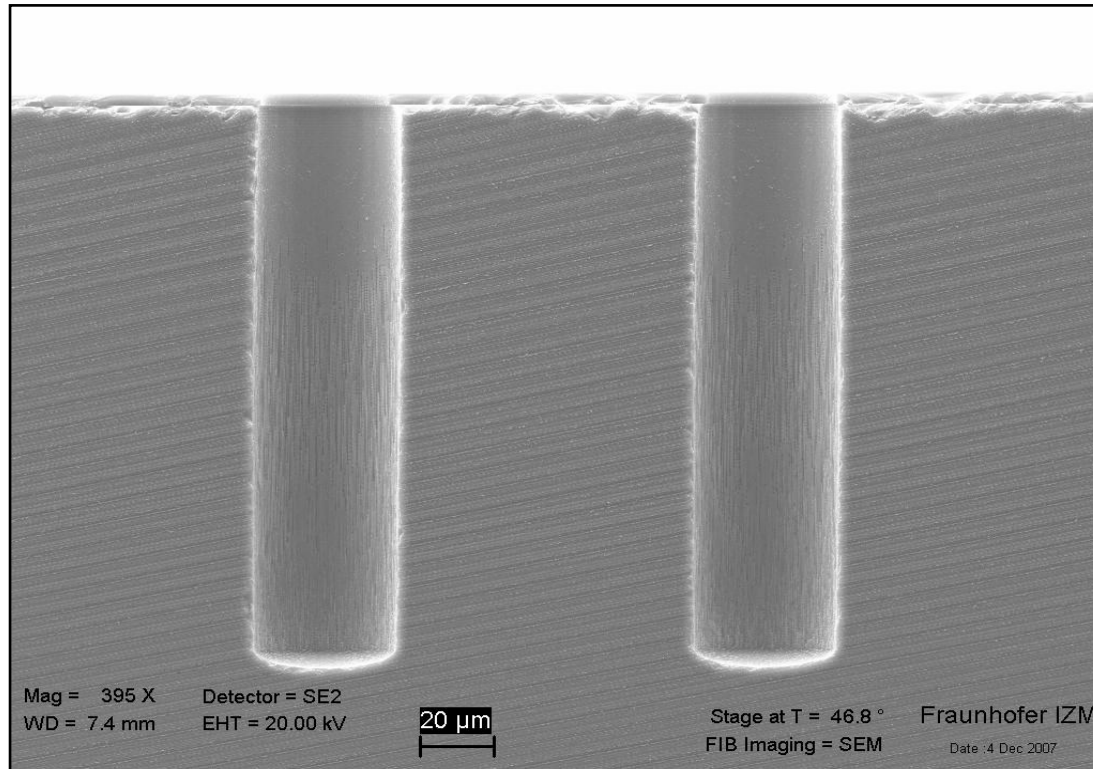
# Deep Via Etching TSV- Test Device – different Via Sizes



40  $\mu\text{m}$  Vias  
80  $\mu\text{m}$  pitch  
depth: 60  $\mu\text{m}$   
CVD-Oxid: 120 nm

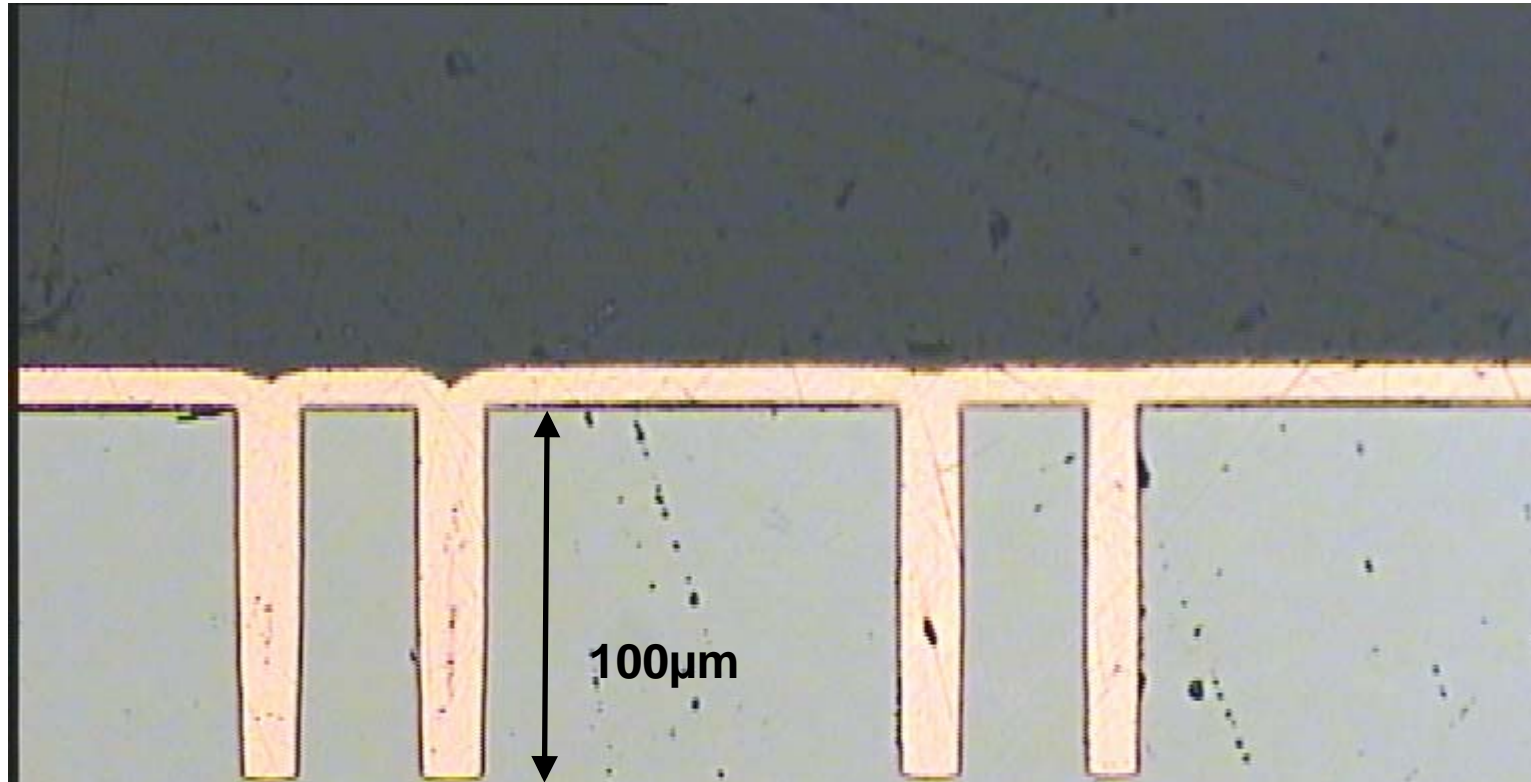


# Via Formation by DRIE (Bosch-Process)



**Silicon via:  $\varnothing$  40 $\mu$ m, depth: 160 $\mu$ m**

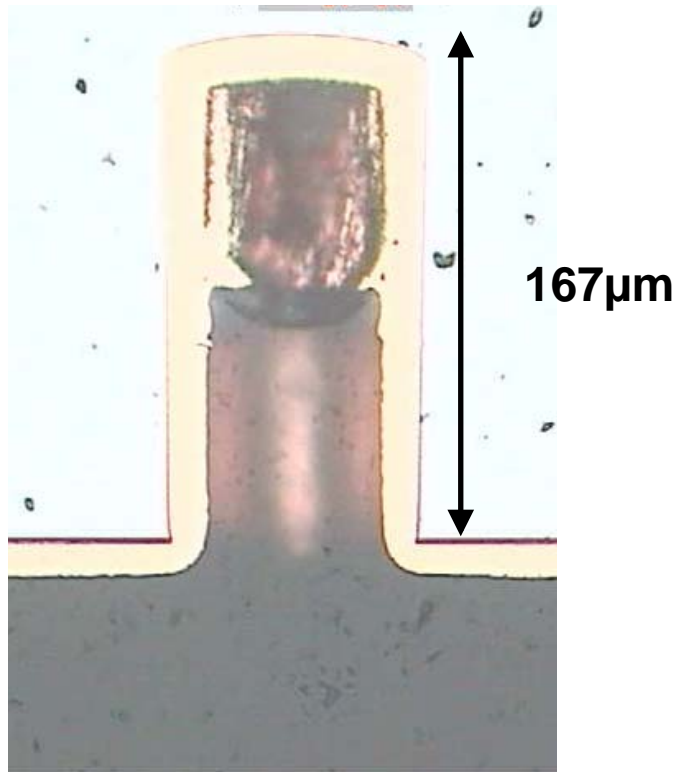
# Through Silicon Via (TSV) Filling Using Electrochemical Deposition of Copper (ECD)



Ø20µm  
Depth: 100µm



# Testwafers for TSVs in FE dies



**Mounting to support wafer**

**Thinning**

**Etching the via from the backside**

**Plating the sidewalls and backside**

**Structuring the backside**

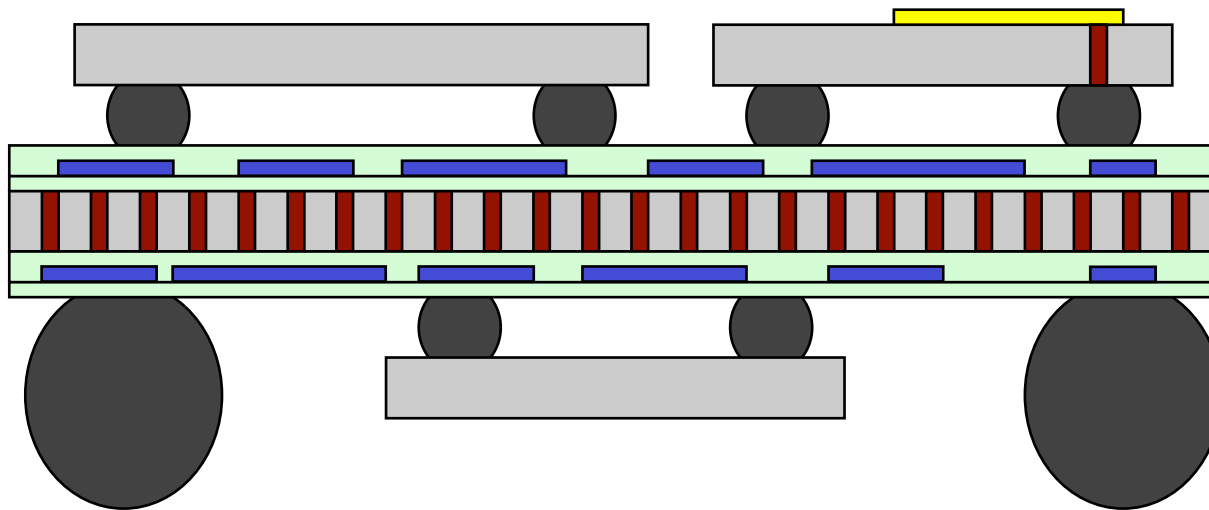
**Supporting from the backside**

**Opening the contact hole to the TSV  
from the frontside**

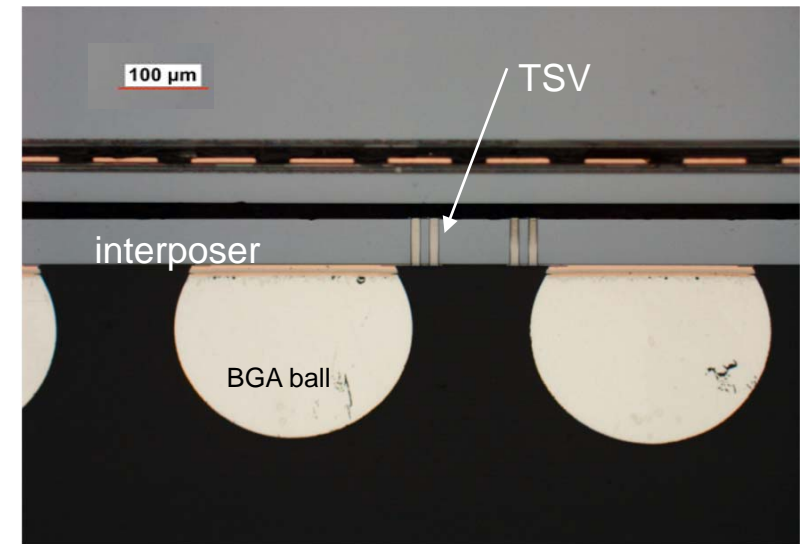
**Metallization on the frontside**



# Silicon Interposers: Driving Force for TSVs



Interposer  
with TSVs



**thank you for  
your attention**

Oswin Ehrmann

Head of Department

**High Density Interconnect & Wafer Level Packaging**

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